

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	1.	4514895	5/7/1985	Nishimura, Tadashi
	2.	4976809	12/11/1990	Broadbent, Eliot K.
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	4.	5417897	5/23/1995	Asakawa, Stuart D. ; McClelland, Paul H. ; Tappon, Ellen R. ; Vandepoll, Richard R. ; Trueba, Kenneth E. ; Chen, Chien Hua
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	8.	5614421	3/25/1997	Yang, Sheng Hsing
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	11.	5620910	4/15/1997	Teramoto, Satoshi
	12.	5710050	1/20/1998	Makita, Naoki ; Miyamoto, Tadayoshi
	13.	5736709	4/7/1998	Neiheisel, Gary L.

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	14.	6093934	7/25/2000	Yamazaki, Shunpei ; Teramoto, Satoshi ; Koyama, Jun ; Ogata, Yasushi ; Hayakawa, Masahiko ; Osame, Mitsuaki ; Ohtani, Hisashi ; Hamatani, Toshiji
	15.	6117301	9/12/2000	Freudenberger, Renate ; Zielonka, Andreas
	16.	6198141	3/6/2001	Yamazaki, Shunpei ; Ohtani, Hisashi ; Fukunaga, Takeshi
	17.	6222195	4/24/2001	Yamada, Akio ; Sagou, Satoru ; Watanabe, Hitoshi ; Yamazaki, Satoru ; Sakamoto, Kiichi ; Ohno, Manabu ; Kawakami, Kenichi ; Kobayashi, Katsuhiko
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	22.	6353218	3/5/2002	Yamazaki, Shunpei ; Tanaka, Koichiro
	23.	6358784	3/19/2002	Zhang, Hongyong ; Yamazaki, Shunpei ; Takemura, Yasuhiko
	24.	6388386	5/14/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio

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	25.	6392810	5/21/2002	Tanaka, Koichiro
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	27.	6410373	6/25/2002	Chang, Ting Chang ; Zan, Hsiao Wen ; Shih, Po Sheng
	28.	6429100	8/6/2002	Yoneda, Kiyoshi
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	33.	6455359	9/24/2002	Yamazaki, Shunpei ; Teramoto, Satoshi ; Kusumoto, Naoto ; Fukunaga, Takeshi ; Nakajima, Setsuo ; Miyamoto, Tadayoshi ; Yoshinouchi, Atsushi
	34.	6471772	10/29/2002	Tanaka, Koichiro
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	36.	6476447	11/5/2002	Yamazaki, Shunpei ; Mase, Akira ; Hiroki, Masaaki ; Takemura, Yasuhiko ; Zhang, Hongyong ; Uochi, Hideki

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	37.	6482722	11/19/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio
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	44.	6521473	2/18/2003	Jung, Yun Ho
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	47.	6563077	5/13/2003	Im, James S.
	48.	6573163	6/3/2003	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
	49.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti

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	52.	6635932	10/21/2003	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
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	54.	6667198	12/23/2003	Shimoto, Shigeyuki ; Uchikoga, Shuichi
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	56.	6734635	5/11/2004	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio
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	63.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun

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	67.	7297982	11/20/2007	Suzuki, Kenkichi ; Nagata, Tetsuya ; Takahashi, Michiko ; Saito, Masakazu ; Ogino, Toshio ; Miyano, Masanobu
	68.	7300858	11/27/2007	Im, James S.
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	72.	20020096680	7/25/2002	Sugano, Yukiyasu ; Fujino, Masahiro ; Mano, Michio ; Asano, Akihiko ; Ino, Masumitsu ; Urazono, Takenobu ; Takatoku, Makoto
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	74.	20020151115	10/17/2002	Nakajima, Hideharu ; Negoro, Yoichi ; Usui, Setsuo
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	76.	20030006221	1/9/2003	Hong, Minghui ; Ye, Kaidong ; An, Chengwu ; Liu, Da Ming

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	80.	20030119286	6/26/2003	Im, James, S. ; Sposili, Robert, S. ; Crowder, Mark, A.
	81.	20030148565	8/7/2003	Yamanaka, Hideo
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	84.	20040140470	7/22/2004	Kawasaki, Ritsuko ; Kasahara, Kenji ; Ohtani, Hisashi
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	86.	20040182838	9/23/2004	Das, Palash, P. ; Bolliger, Bruce, E. ; Patel, Parthiv, S. ; Klene, Brian, C. ; Melcher, Paul, C. ; Saethre, Robert, B.
	87.	20040222187	11/11/2004	Lin, Kun Chih
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	89.	20050059265	3/17/2005	Im, James

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
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	91.	20050142450	6/30/2005	Jung, Yun
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	93.	20050202654	9/15/2005	Im, James
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	101.	20070032096	2/8/2007	Im, James, S.
	102.	20070108472	5/17/2007	Jeong, Jae, Kyeong ; Shin, Hyun, Soo ; Kwon, Se, Yeoul ; Mo, Yeon, Gon
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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
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	108.	JP11281997 (with English machine translation)	10/15/1999	GOTO YASUMASA ; IMAI NOBUO
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